



# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





# BT151X-650C

SCR

16 March 2014

Product data sheet

## 1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT186A (TO-220F) "full pack" plastic package intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance.

## 2. Features and benefits

- High bidirectional blocking voltage capability
- High thermal cycling performance
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability

## 3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation

## 4. Quick reference data

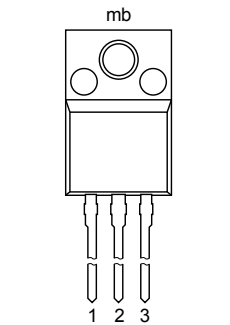

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	650	V
$V_{RRM}$	repetitive peak reverse voltage		-	-	650	V
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	100	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_h \leq 69\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	12	A
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	2	15	mA



## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p>mb</p> <p>TO-220F (SOT186A)</p>	 <p>A K G sym037</p>
2	A	anode		
3	G	gate		
mb	n.c.	mounting base; isolated		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT151X-650C	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	650	V
$V_{RRM}$	repetitive peak reverse voltage		-	650	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_h \leq 69\text{ }^\circ\text{C}$	-	7.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_h \leq 69\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	12	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	100	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 8.3\text{ ms}$	-	110	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	50	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_T = 20\text{ A}$ ; $I_G = 50\text{ mA}$ ; $di_G/dt = 50\text{ mA}/\mu\text{s}$	-	50	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		-	2	A

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	125	°C

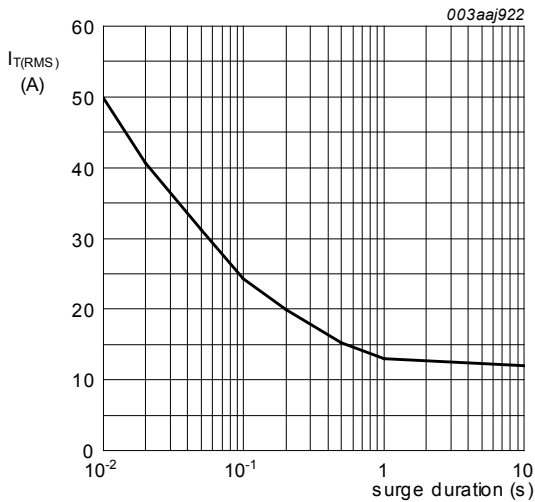


Fig. 1. RMS on-state current as a function of surge duration; maximum values

$f = 50 \text{ Hz}; T_h = 69 \text{ °C}$

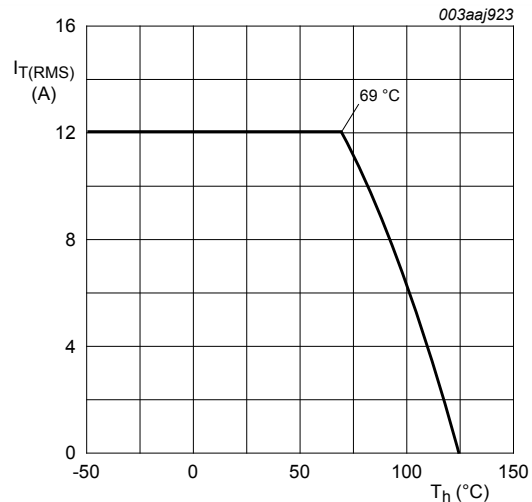


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values

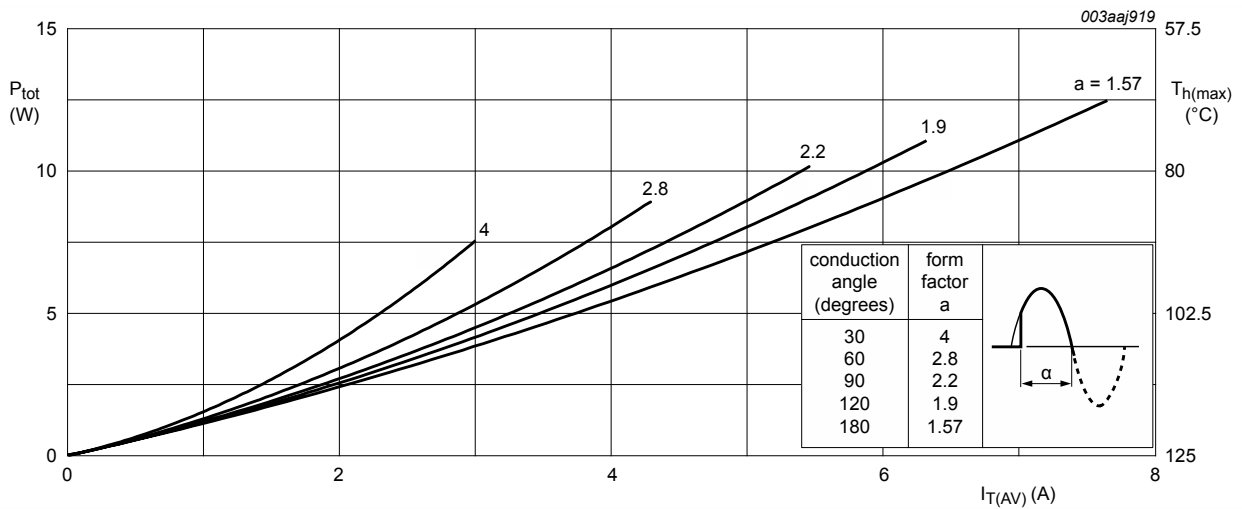
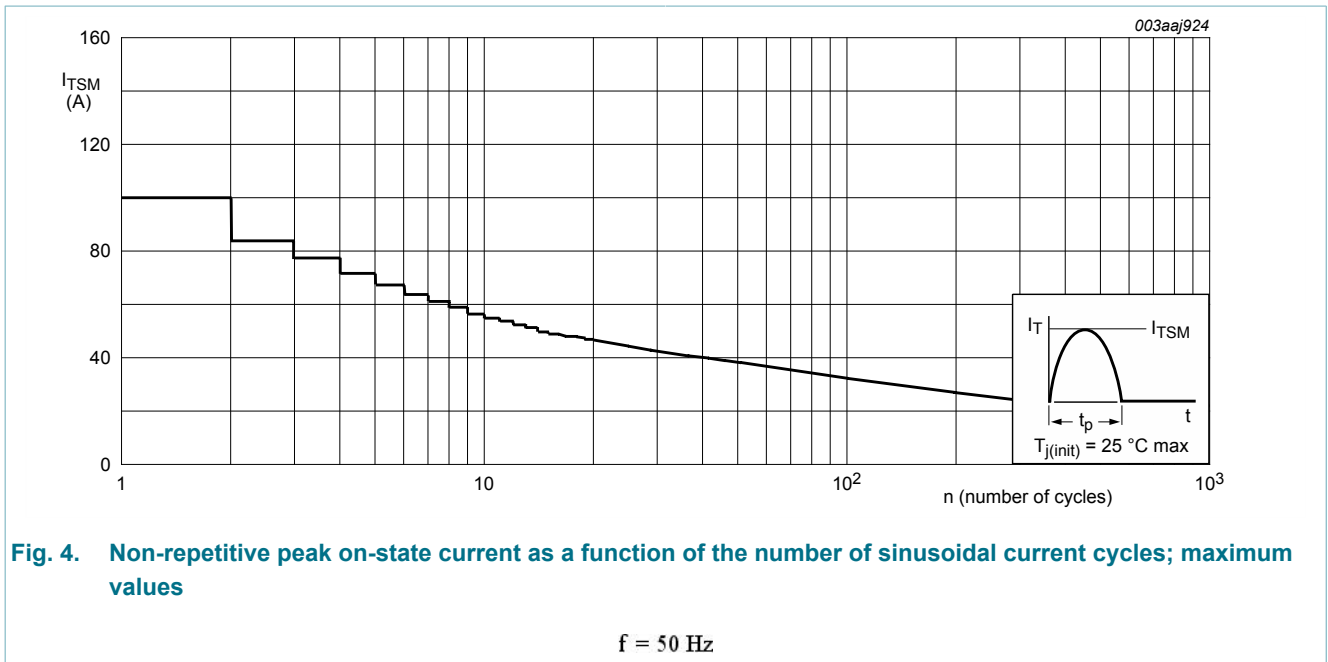
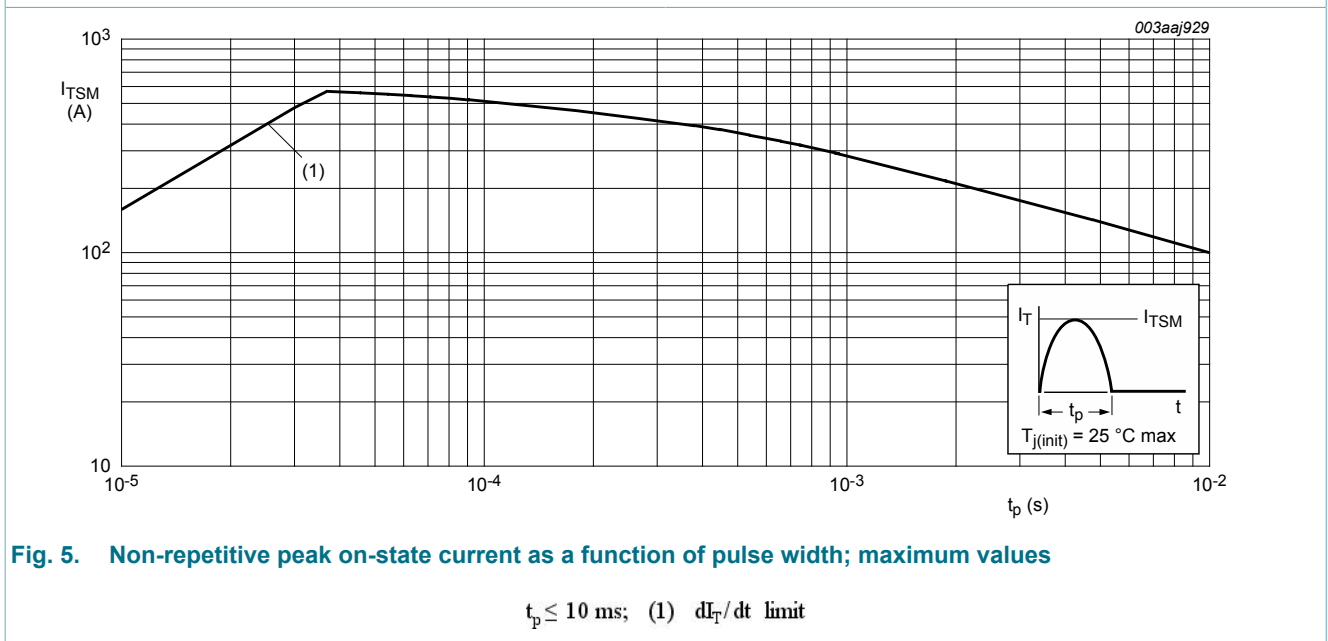


Fig. 3. Total power dissipation as a function of average on-state current; maximum values

$\alpha = \text{conduction angle}$      $a = \text{form factor} = I_{T(RMS)} / I_{T(AV)}$



**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**

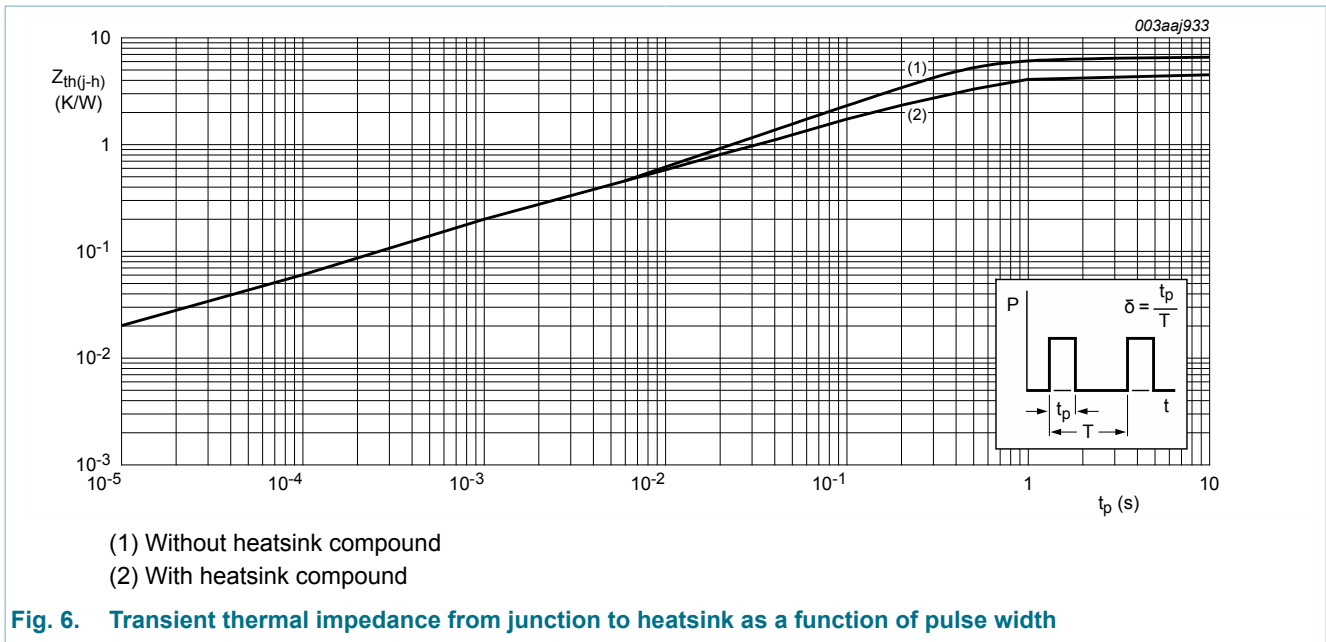


**Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values**

## 8. Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; <a href="#">Fig. 6</a>	-	-	4.5	K/W
		without heatsink compound; <a href="#">Fig. 6</a>	-	-	6.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



## 9. Isolation characteristics

**Table 6. Isolation characteristics**

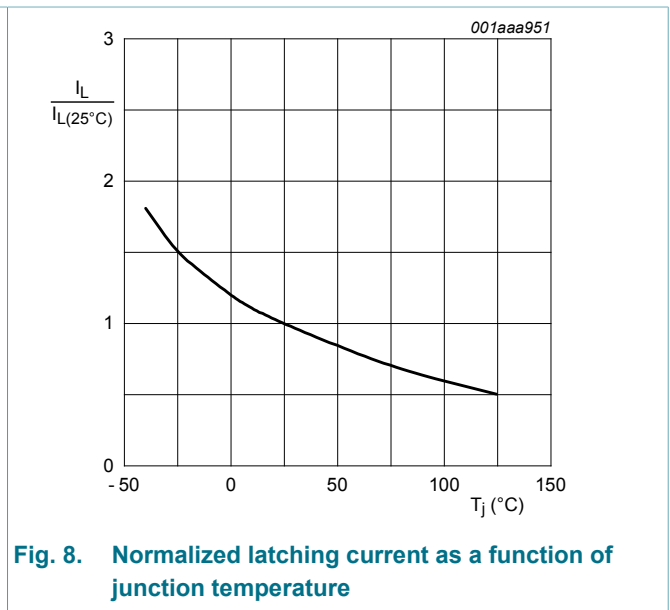
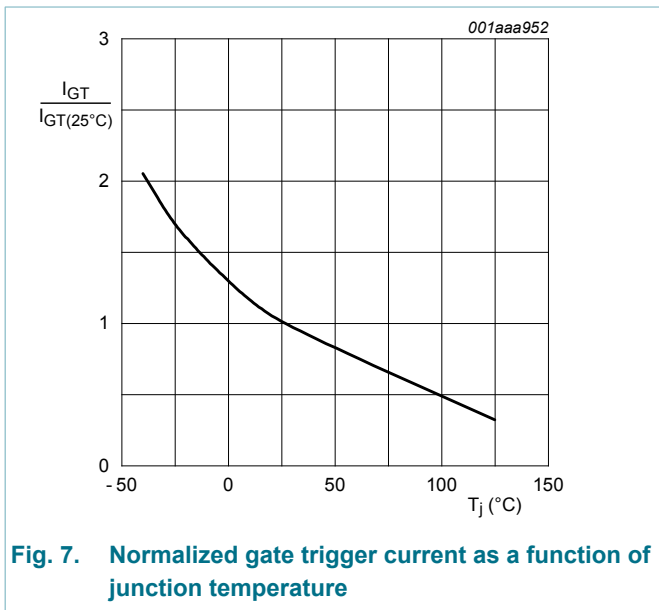
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$ ; $RH \leq 65\%$ ; $T_h = 25\text{ }^\circ\text{C}$	-	-	2500	V
$C_{isol}$	isolation capacitance	from anode to external heatsink; $f = 1\text{ MHz}$ ; $T_h = 25\text{ }^\circ\text{C}$	-	10	-	pF

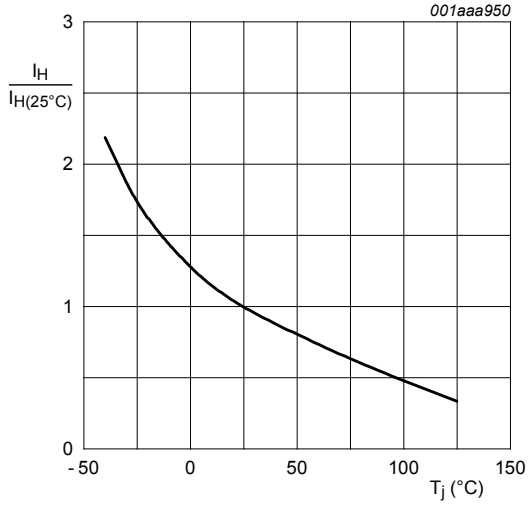
## 10. Characteristics

**Table 7. Characteristics**

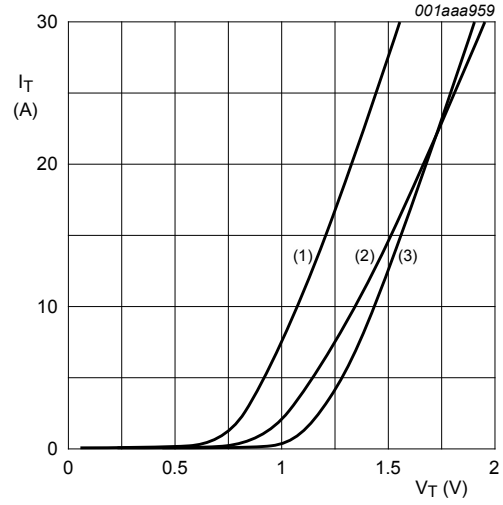
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	2	15	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	-	10	40	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	7	20	mA
$V_T$	on-state voltage	$I_T = 23\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>	-	1.4	1.75	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	0.6	1	V
		$V_D = 650\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	0.25	0.4	-	V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_D$	off-state current	$V_D = 650\text{ V}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
$I_R$	reverse current	$V_R = 650\text{ V}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 436\text{ V}; T_j = 125\text{ }^\circ\text{C}; R_{GK} = 100\text{ }\Omega;$ ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; <a href="#">Fig. 12</a>	200	1000	-	V/ $\mu$ s
		$V_{DM} = 436\text{ V}; T_j = 125\text{ }^\circ\text{C};$ ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 12</a>	50	130	-	V/ $\mu$ s
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 40\text{ A}; V_D = 650\text{ V}; I_G = 100\text{ mA};$ $di_G/dt = 5\text{ A}/\mu\text{s}; T_j = 25\text{ }^\circ\text{C}$	-	2	-	$\mu$ s
$t_q$	commutated turn-off time	$V_{DM} = 436\text{ V}; T_j = 125\text{ }^\circ\text{C}; I_{TM} = 20\text{ A};$ $V_R = 25\text{ V}; (di_T/dt)_M = 30\text{ A}/\mu\text{s}; dV_D/dt = 50\text{ V}/\mu\text{s};$ $R_{GK} = 100\text{ }\Omega;$ ( $V_{DM} = 67\%$ of $V_{DRM}$ )	-	70	-	$\mu$ s





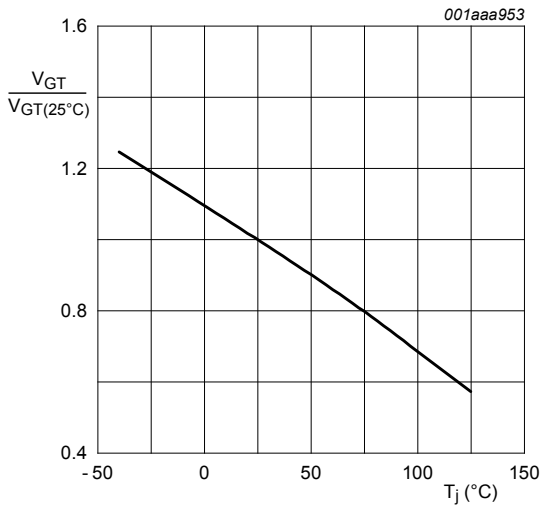
**Fig. 9. Normalized holding current as a function of junction temperature**



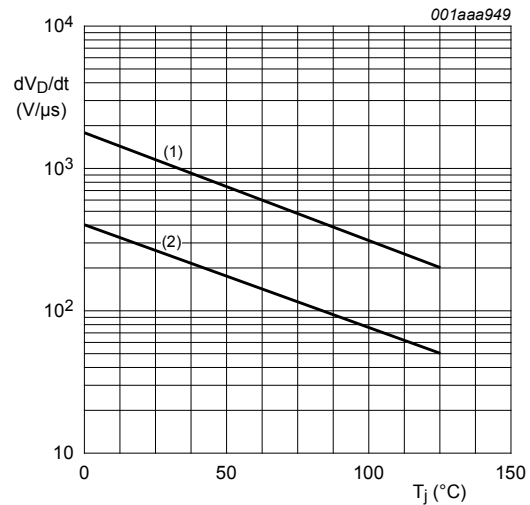
$V_o = 1.06 \text{ V}; R_s = 0.0304 \Omega$

- (1)  $T_j = 125 \text{ }^\circ\text{C}$ ; typical values
- (2)  $T_j = 125 \text{ }^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

**Fig. 10. On-state current as a function of on-state voltage**



**Fig. 11. Normalized gate trigger voltage as a function of junction temperature**



- (1)  $R_{GK} = 100 \Omega$ ;
- (2) gate open circuit

**Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values**



### 11. Package outline

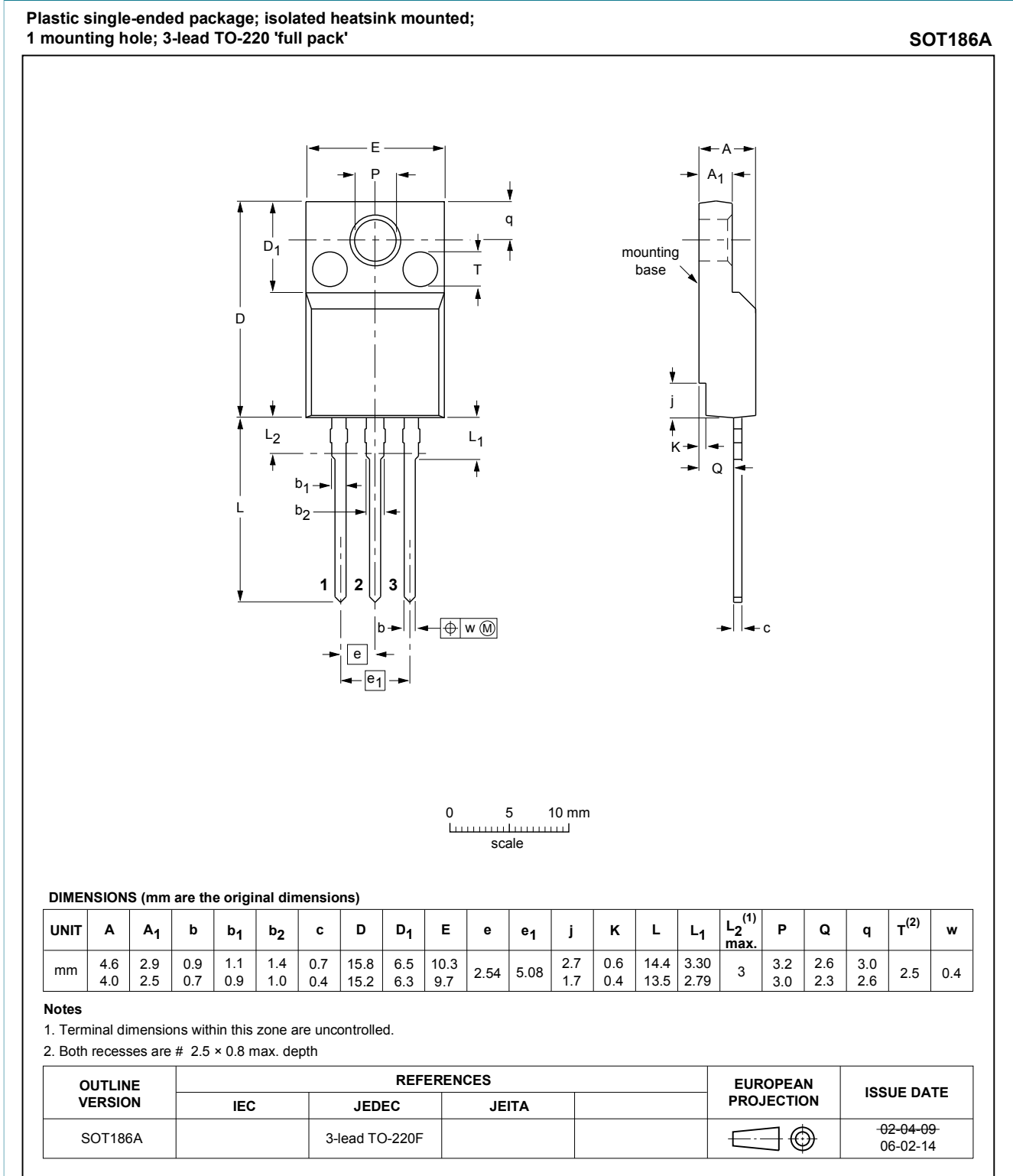


Fig. 13. Package outline TO-220F (SOT186A)

## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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